

# VS-8ETH06SPbF, VS-8ETH06-1PbF

# Vishay Semiconductors

DYNAMIC RECOVERY CHARAC	$I_{F} = 1 \text{ A, } dI_{F}/dt = 100 \text{ A/}\mu\text{s, } V_{R} = 30 \text{ V} \qquad - \qquad 18 \qquad 22$ $I_{F} = 8 \text{ A, } dI_{F}/dt = 100 \text{ A/}\mu\text{s, } V_{R} = 30 \text{ V} \qquad - \qquad 20 \qquad 25$ ns						
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V <sub>R</sub> = 30 V	-	18	22	
Payarea rasayary tima		$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	20	25	1 ,,,
neverse recovery time	L <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	115
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	-	40	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.4	-	Α
		T <sub>J</sub> = 125 °C		-	4.8	-	
Deverse vecessors shares	0	T <sub>J</sub> = 25 °C			-	25	-
Reverse recovery charge	very charge $Q_{rr}$ $T_J = 125 ^{\circ}C$	-	120	-	i iiC		
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$dI_F/dt = 600 A/\mu s$	-	12	-	Α
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	220	-	nC

THERMAL - MECHANICAL S	SPECIFICATION	ONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per leg	$R_{thJC}$		-	1.4	2	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	ı	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-263AB (D <sup>2</sup> PAK)		8ETH06S		
		Case style TO-262AA	8ETH06-1			



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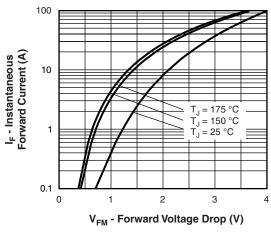


Fig. 1 - Maximum Forward Voltage Drop Characteristics

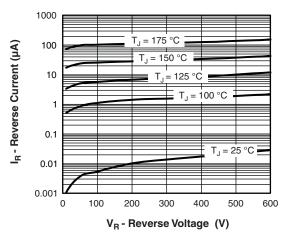


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

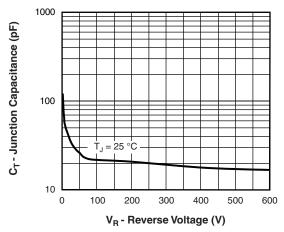


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

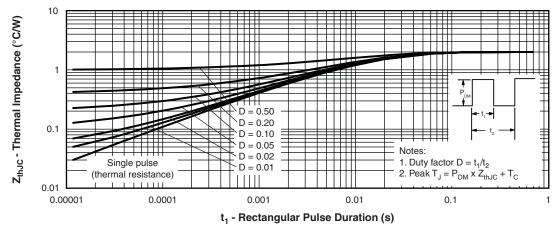


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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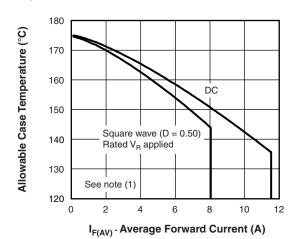


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

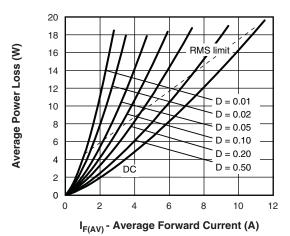


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

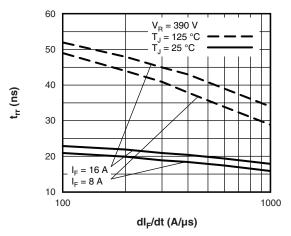


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

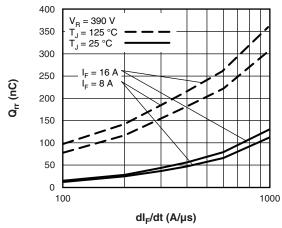


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



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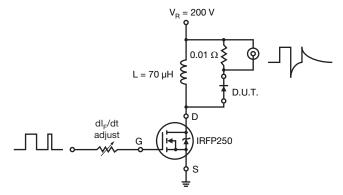
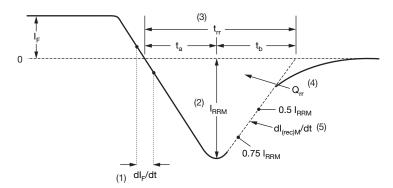


Fig. 9 - Reverse Recovery Parameter Test Circuit



- dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

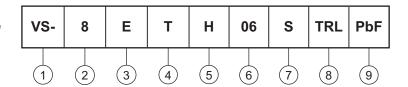
Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (8 A)

3 - E = single diode

- T = TO-220, D<sup>2</sup>PAK

5 - H = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - • S = D<sup>2</sup>PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)

9 - PbF = lead (Pb)-free

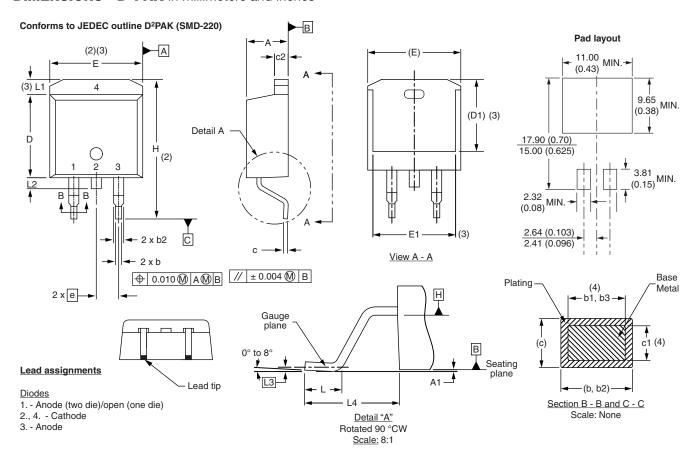
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95014</u>				
Part marking information	www.vishay.com/doc?95008			
Packaging information	www.vishay.com/doc?95032			



## Vishay Semiconductors

# **D<sup>2</sup>PAK, TO-262**

## **DIMENSIONS - D<sup>2</sup>PAK** in millimeters and inches



SYMBOL	MILLIMETERS		INC	NOTEO	
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIN	IETERS	INC	NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$  Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

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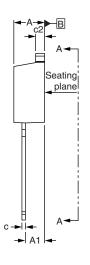
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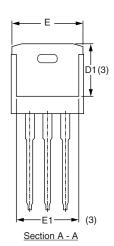
D<sup>2</sup>PAK, TO-262



#### **DIMENSIONS - TO-262** in millimeters and inches

# Modified JEDEC outline TO-262 (Datum A) (2) (3) (3) 1 D D L2 B B B B L (2) A 3 x b2 3 x b2 3 x b





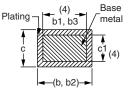
⊕|0.010@|A@|B

Lead assignments

### Diodes

1. - Anode (two die)/open (one die) 2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIMETERS		INC	NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

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